

03/76-UPS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Gou-Chung Chi, Iinn-Kong Sheu, Meng-Che Chen and Min-Lum
Date : Lee
Serial No. :
Group Art Unit:
Filed :
For : ULTRAVIOLET DETECTOR AND MANUFACTURE METHOD THEREOF

Honorable Commissioner of Patents
and Trademarks
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

Attached is a completed Form PTO-1449 and copies of the pertinent parts of the references cited thereon. Comments on any non-English-language references (if any) pursuant to Rule are submitted herewith.

Respectfully submitted

Applicants(s): G. C. Chi I. Kong Sheu Meng-Che Chen
Min-Lum Lee

Encl: PTO-1449 & References

| FORM PTO-1449 (Substitute) | | | ATTY. DOCKET NO. 03176-UPS | SERIAL NO. | | | |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------|------------|-------|----------|----------------------------|
| LIST OF PRIOR ART CITED BY APPLICANT <i>(Use several sheets if necessary)</i> | | | APPLICANT Gou-Chung Chi et al. | | | | |
| | | | FILING DATE | GROUP | | | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| *EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
| | AA | | | | | | |
| | AB | | | | | | |
| | AC | | | | | | |
| | AD | | | | | | |
| | AE | | | | | | |
| | AF | | | | | | |
| | AG | | | | | | |
| | AH | | | | | | |
| | AI | | | | | | |
| | AJ | | | | | | |
| | AK | | | | | | |
| FOREIGN PATENT DOCUMENTS | | | | | | | |
| | AL | | | | | | |
| | AM | | | | | | |
| | AN | | | | | | |
| | AO | | | | | | |
| | AP | | | | | | |
| OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | |
| | AR | Planar GaN n ⁺ -p photodetectors formed by Si implantation into p-GaN | | | | | |
| | | J. K. Sheu, M. L. Lee, L. S. Yeh, C. J. Kao, C. J. Tun, M. G. Chen, G. C. Chi, S. J. Chang, Y. K. Su, and C. T. Lee Department of Physics, National Central University, Chung-Li 320, Taiwan, Republic of China (Received 6 May 2002; accepted 7 October 2002) | | | | | |
| | AS | | | | | | |
| | | | | | | | |
| | AT | | | | | | |
| | | | | | | | |
| EXAMINER | | | DATE CONSIDERED | | | | |
| <small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small> | | | | | | | |